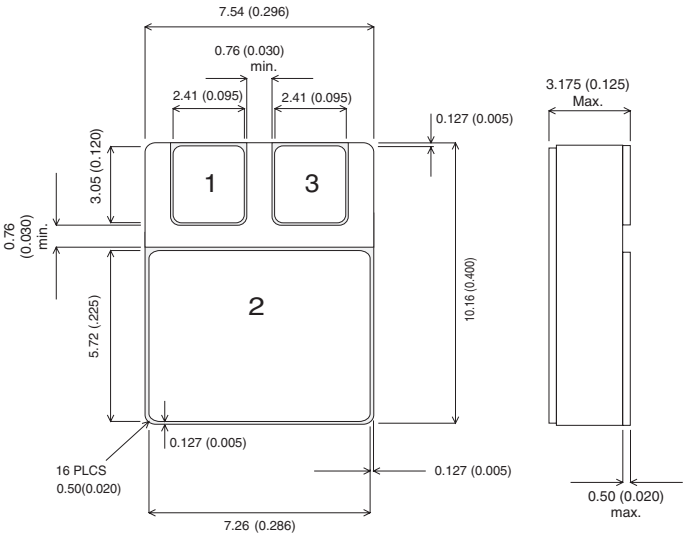
IRFNJ130
IRFN130SMD05

MECHANICAL DATA
Dimensions in mm (inches)



SMD05 (TO-276AA)

IRFNJ130
PAD1 = GATE PAD 2 DRAIN PAD3 = SOURCE

IRFN130SMD05
PAD1 = SOURCE PAD 2 = DRAIN PAD3 = GATE

N–CHANNEL POWER MOSFET FOR HI–REL APPLICATIONS

V_{DSS}	100V
$I_{D(cont)}$	11A
$R_{DS(on)}$	0.19Ω

FEATURES
- HERMETICALLY SEALED
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT
- SCREENING OPTIONS AVAILABLE
- ALL LEADS ISOLATED FROM CASE

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{GS}	Gate – Source Voltage	±20V
I_D	Continuous Drain Current @ T_{case} = 25°C	11A
I_D	Continuous Drain Current @ T_{case} = 100°C	7A
I_{DM}	Pulsed Drain Current	44A
P_D	Power Dissipation @ T_{case} = 25°C	45W
	Linear Derating Factor	0.36W/°C
T_J , T_{stg}	Operating and Storage Temperature Range	–55 to 150°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	2.8°C/W max.

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Semelab plc. Telephone +44(0)1455 556565. Fax +44(0)1455 552612.
E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk

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SEME LAB

IRFNJ130
IRFN130SMD05

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
	STATIC ELECTRICAL RATINGS						
BV_{DSS}	Drain – Source Breakdown Voltage	V_{GS} = 0	I_D = 1mA	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I_D = 1mA			0.1		V/°C
$R_{DS(on)}$	Static Drain – Source On–State Resistance	V_{GS} = 10V	I_D = 7A			0.19	Ω
		V_{GS} = 10V	I_D = 11A			0.22	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$	I_D = 250µA	2		4	V
g_{fs}	Forward Transconductance	$V_{DS} \geq 15V$	I_{DS} = 7A	3			S(℧)
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0	$V_{DS} = 0.8BV_{DSS}$			25	µA
			T_J = 125°C			250	
I_{GSS}	Forward Gate – Source Leakage	V_{GS} = 20V				100	nA
I_{GSS}	Reverse Gate – Source Leakage	V_{GS} = –20V				-100	
	DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0			650		pF
C_{oss}	Output Capacitance	V_{DS} = 25V			240		
C_{rss}	Reverse Transfer Capacitance	f = 1MHz			44		
Q_g	Total Gate Charge	V_{GS} = 10V $V_{DS} = 0.5BV_{DSS}$	I_D = 11A	12.8		28.5	nC
Q_{gs}	Gate – Source Charge	I_D = 11A		1.0		6.3	nC
Q_{gd}	Gate – Drain (“Miller”) Charge	$V_{DS} = 0.5BV_{DSS}$		3.8		16.6	
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 50V I_D = 11A R_G = 7.5Ω				30	ns
t_r	Rise Time					75	
$t_{d(off)}$	Turn–Off Delay Time					40	
t_f	Fall Time					45	
	SOURCE – DRAIN DIODE CHARACTERISTICS						
I_S	Continuous Source Current					11	A
I_{SM}	Pulse Source Current					43	
V_{SD}	Diode Forward Voltage	I_S = 11A V_{GS} = 0	T_J = 25°C			1.5	V
t_{rr}	Reverse Recovery Time	I_S = 11A	T_J = 25°C			300	ns
Q_{rr}	Reverse Recovery Charge	$d_i / d_t \leq 100A/\mu s$	$V_{DD} \leq 50V$			3	µC
	PACKAGE CHARACTERISTICS						
L_D	Internal Drain Inductance (from 6mm down drain lead pad to centre of die)				8.7		nH
L_S	Internal Source Inductance (from 6mm down source lead to centre of source bond pad)				8.7		

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